

Form PTO-1449 (MODIFIED)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. 039153-0450 (G1155)	SERIAL NO. 10/016,273		
O I P INFORMATION DISCLOSURE CITATION				APPLICANT Lukanc et al.			
JUN 02 2003 (Use several sheets if necessary)				FILING DATE 12/11/2001	GROUP ART UNIT 1756		
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB-CLASS	FILING DATE IF APPROPRIATE
<i>DR</i>	A1	6,410,193	6/25/2002	Stivers et al.	430	5	<i>RECEIVED JUN 05 2003</i>
<i>DR</i>	A2	6,013,399	1/11/00	Nguyen	430	5	
<i>DR</i>	A3	5,861,233	1/19/99	Sekine et al.	430	2960	
<i>DR</i>	A4	5,780,187	7/14/98	Pierrat	430	5	
<i>DR</i>	A5	5,641,593	6/24/97	Watanabe et al.	430	5	
<i>DR</i>	A6	5,619,059	4/8/97	Li et al.	257	431	
<i>DR</i>	A7	5,328,784	7/12/1994	Fukuda	430	5	
FOREIGN PATENT DOCUMENTS							
	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB-CLASS	TRANSLATION
							YES
<i>DR</i>	A8	EP 0 708 367 B1	14-01-1998	European			
EXAMINER <i>DR</i> <i>Coasey</i>				DATE CONSIDERED <i>8/27/03</i>			

- * EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include any copy of this form with next communication to applicant.

Form PTO-1449 (MODIFIED)	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. 039153-0450 (G1155)	SERIAL NO. 10/016,278
O I P E INFORMATION DISCLOSURE CITATION JUN 02 2003 (Use several sheets if necessary)		APPLICANT Lukanc et al.	RECEIVED JUN 05 2003 PC 1700
		FILING DATE 12/11/2001	

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

	B9	T. BRUNNER ET AL., "170 nm gates fabricated by phase-shift mask and top anti-reflector process," 182/SPIE Vol. 1927, Optical/Laser Microlithography VI, 1993, pps. 1-8.
	B10	KURT RONSE ET AL., "Comparison of various phase shift strategies and application to 0.35 μ m ASIC Designs," 2/SPIE Vol. 1927, Optical/Laser Microlithography VI, 1993, pps. 1-15.
	B11	J. M. CALVERT ET AL., "Projection X-Ray Lithography With Ultrathin Imaging Layers and Selective Electroless Metallization," Optical Engineering Vol. 32 No. 10, Oct. 1993., pp. 2437-2445
	B12	H. KYURAGI ET AL., "Synchrotron Radiation-Excited Chemical Vapor Deposition of Silicon Nitride Films from a SiH ₄ + NH ₃ Gas Mixture," Journal of the Electrochemical Society, Vol. 138 No. 11, Nov. 1991, pp. 3412-3416.
	B13	Y. MATSUI ET AL., "Low-Temperature Growth of SiO ₂ Thin Film by Photo-Induced Chemical Vapor Deposition Using Synchrotron Radiation," Japanese Journal of Applied Physics, Part I, Vol. 31 n.6B, June 1992, pp. 1972-1978.
	B14	J. F. MOORE ET AL., "Deposition of Dielectric Thin Films by Irradiation of Condensed Reactant Mixtures," Materials Research Society Symposium Proceedings, Vol. 335, 1994, pp. 81-86.
	B15	I. NISHIYAMA ET AL., "Photon Energy Dependence of Synchrotron Radiation Induced Growth Suppression and Initiation in Al Chemical Vapor Deposition II. Surface Analysis by Auger Electron Spectroscopy," Applied Surface Science, Vol. 103, 1996, pp. 299-306
	B16	O. R. WOOD II ET AL., "Use of Attenuated Phase Masks in Extreme Ultraviolet Lithography," Journal of Vacuum Science and Technology B, Vol. 15, No. 6, Nov/Dec 1997, pp. 2448-2451
	B17	R. ZANONI ET AL., "Synchrotron-Radiation-Stimulated Tungsten Deposition on Silicon from W(CO) ₆ ," Journal of Vacuum Science and Technology A, Vol. 9, No. 3, May/June 1991, pp. 931-934.
	B18	CHEN HL ET AL., "Simulation on a New Reflection Type Attenuated Phase Shifting Mask for Extreme Ultraviolet Lithography", Emerging Lithographic Technologies III, Santa Clara, CA, USA, 15-17 March 1999, Vol. 3676, pages 578-586, XP002230586, Proceedings of the SPIE - The International Society for Optical Engineering, 1999, SPIE - Int. Soc. Opt. Eng., USA,

8/27/03